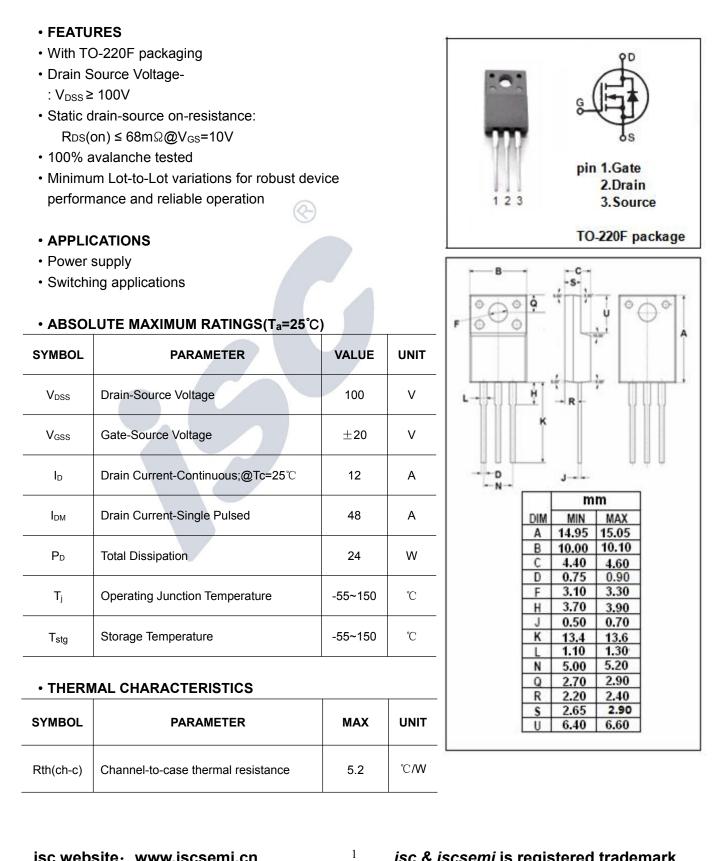


INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

FDPF680N10T



isc website: www.iscsemi.cn



isc N-Channel MOSFET Transistor

FDPF680N10T

ELECTRICAL CHARACTERISTICS

$T_{\rm C}\text{=}25^\circ\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 250uA	100			V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =250uA	2.5		4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 6A			68	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 100V; V _{GS} = 0V V _{DS} = 100V; V _{GS} = 0V;T _J =150°C			1 500	μA
V _{SDF}	Diode forward voltage	I _{SD} = 12A, V _{GS} = 0 V			1.3	V

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